PE					Docket Number (Optional) BUR920020020U		Application Number 09/683,9	83	#4
INFORMATION DISCLOSURE CITATION Use several sheets if necessary)					Applicant(s) Jagannathan et al.		Group Art Unit OF PAPERED OFFICINALLY FILED		
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				OTHER D	OCUMENTS (Including A	uthor, Title,	Date, Pertinent Pag	es, Etc.)	<u> </u>
L. D. Lanzerotti et al., "Suppression of Boron Outdiffusion in SiGe HBTs by Carbon Incorporation", 1996 IEEE 96-249, pp. 10.2.1-10.2.4								996 IEEE,	IEDM
MLT		S. R. Stiffler et al., "The role of dislocation-dislocation interactions in the relaxation of pseudomorphically strained semiconductors. II. Experiment The high-temperature relaxation of ultrahigh-vacuum chemical-vapor-deposited SiGe							
MLT		films" J. Appl. Phys. 71 (10), 15 May 1992 p. 4820-4825 J. W. Matthews et al., " Defects in Epitaxial Multilayers", Journal of Crystal Growth 27 (1974), pp. 118-125							
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EXAMINER Minhloan Train					DATE CONSIDERED	5/5	2003		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

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